



US 20240251568A1

(19) **United States**

(12) **Patent Application Publication**  
**Peng et al.**

(10) **Pub. No.: US 2024/0251568 A1**

(43) **Pub. Date: Jul. 25, 2024**

(54) **SEMICONDUCTOR DEVICE WITH  
MAGNETIC TUNNEL JUNCTIONS**

(60) Provisional application No. 62/753,659, filed on Oct. 31, 2018.

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**Publication Classification**

(51) **Int. Cl.**  
**H10B 61/00** (2006.01)  
**G11C 11/16** (2006.01)  
**H10N 50/01** (2006.01)  
**H10N 50/10** (2006.01)

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(52) **U.S. Cl.**  
CPC ..... **H10B 61/22** (2023.02); **H10N 50/01**  
(2023.02); **H10N 50/10** (2023.02); **G11C**  
**11/1659** (2013.01)

(21) Appl. No.: **18/626,670**

(57) **ABSTRACT**

(22) Filed: **Apr. 4, 2024**

**Related U.S. Application Data**

(60) Division of application No. 17/346,855, filed on Jun. 14, 2021, now Pat. No. 11,980,040, which is a continuation of application No. 16/560,623, filed on Sep. 4, 2019, now Pat. No. 11,037,981.

A semiconductor device includes a substrate; a memory array over the substrate, the memory array including first magnetic tunnel junctions (MTJs), where the first MTJs are in a first dielectric layer over the substrate; and a resistor circuit over the substrate, the resistor circuit including second MTJs, where the second MTJs are in the first dielectric layer.

